

Flash Memory Summit 2013 Plenary Session: Flash Below 20 nm: What is Coming and When

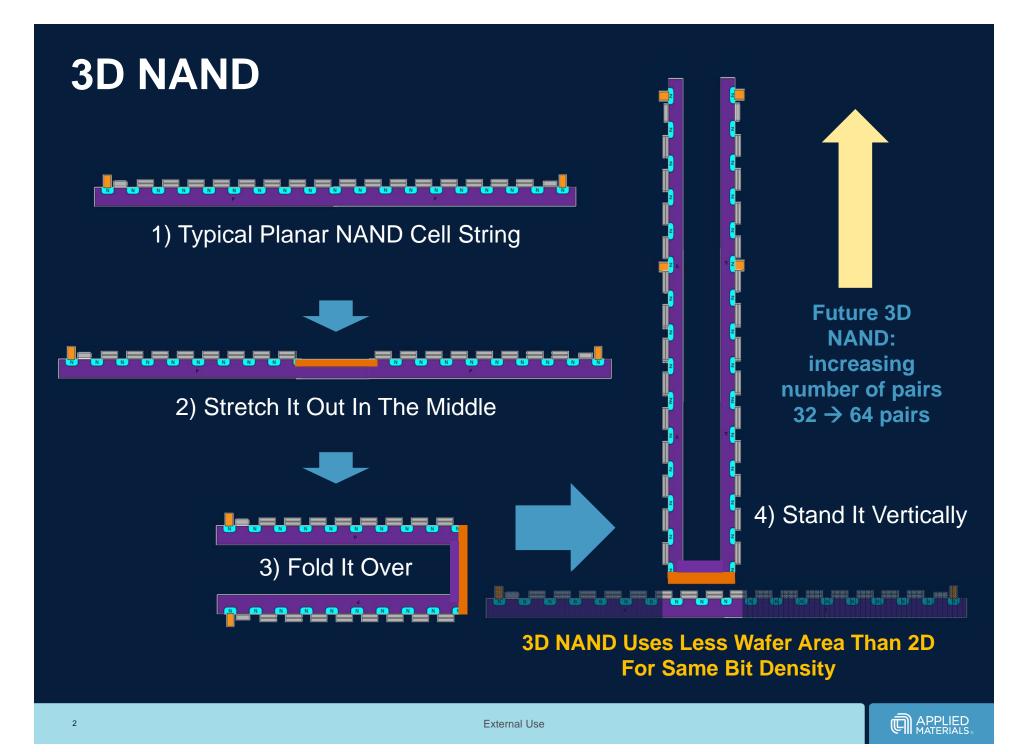
Challenges in 3D NAND

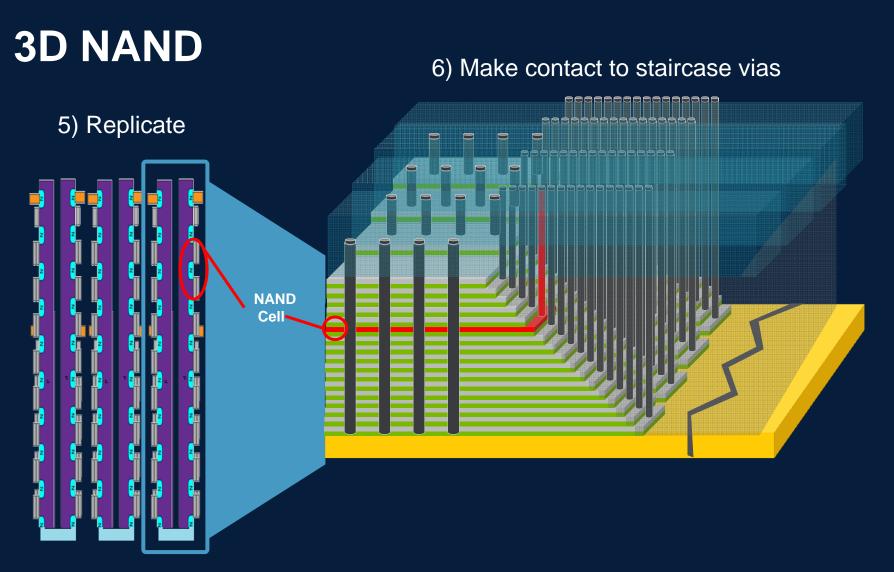


Gill Lee

Senior Director / Principal Member of Technical Staff Silicon Systems Group Applied Materials, Inc.







3D NAND does not require leading-edge lithography, but it will require new deposition and etch technologies.

3D NAND: Game Changer for Etch and Deposition PLANAR 3D NAND CD DEFINITION AND SCALING CD DEFINITION AND SCALING (~50nm) (<15nm) Etch and Deposition Grows Lithography Lithography drops **ETCH ETCH** 2 Lower aspect ratios High aspect ratios Staircase patterning (trim and etch) Multi-patterning (SATP, SAQP) DEPOSITION **DEPOSITION** Single layer Multi-layer stacks 3 Thinner films Thick films (active and hardmask)

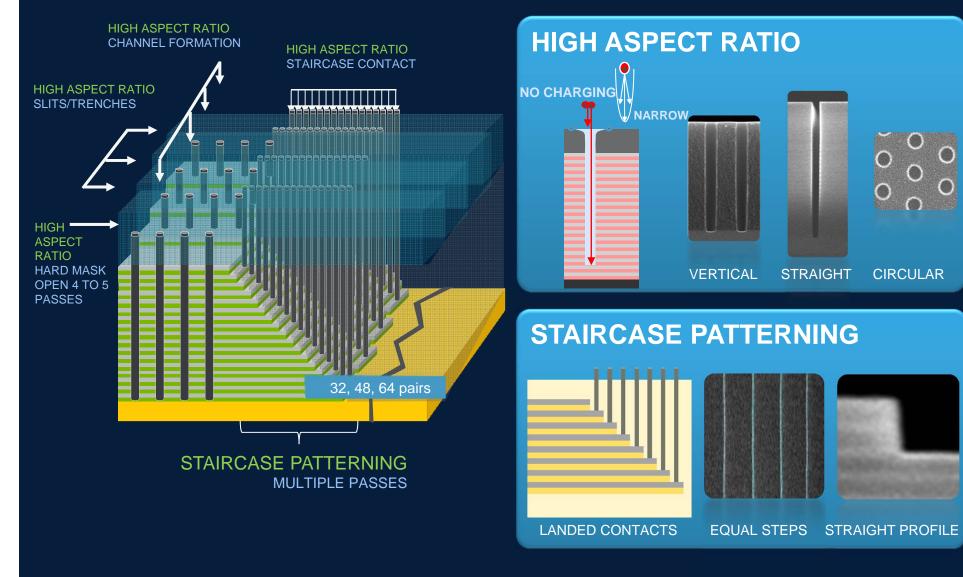


4

External Use

APPLIED MATERIALS

3D NAND: New Etch Applications



5

CIRCULAR

3D NAND: New CVD Applications

Critical Hardmask

Channel, Word Line, Metal Contact High Aspect Ratios up to 60:1

Gate Stack

Oxide/Nitride or Silicon

CVD Gapfill

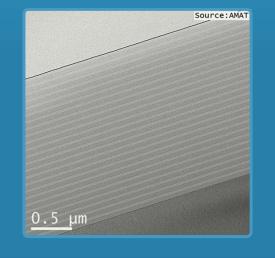
Isolation and Interlayer Dielectrics

Gate Stack Challenges:

- Film Thickness determines Gate Length; Uniformity is Critical
- Manufacturing costs will pace adoption due to lower throughputs

Gate Stack Solution:

- Innovative Precision CVD Chamber Design with
 - Uniform deposition with layer-to-layer precision
 - > Superior repeatability with independent station control
 - Higher Chamber throughput efficiency with lower operating cost





Sources: VLSI and IEDM

External Use

